

SPTECH Silicon PNP Power Transistor**2SA968****DESCRIPTION**

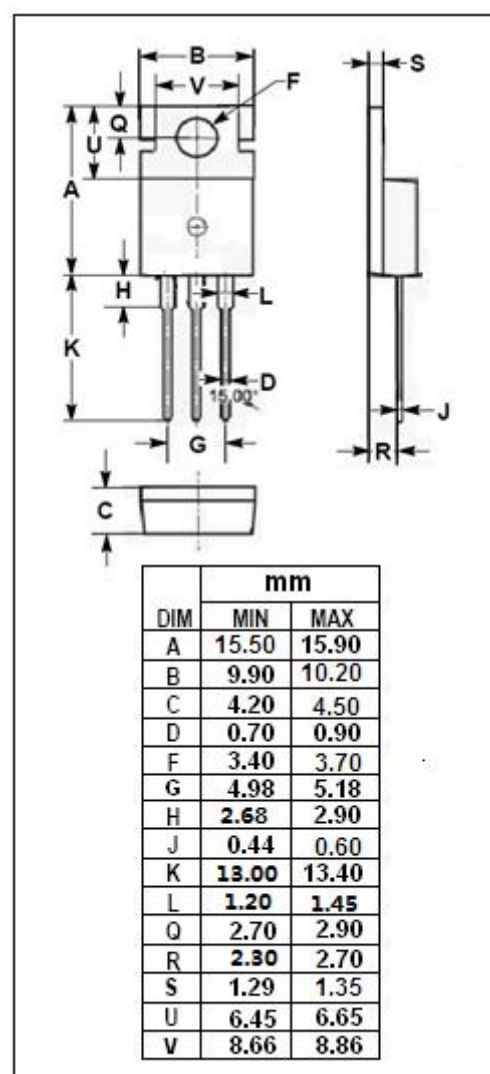
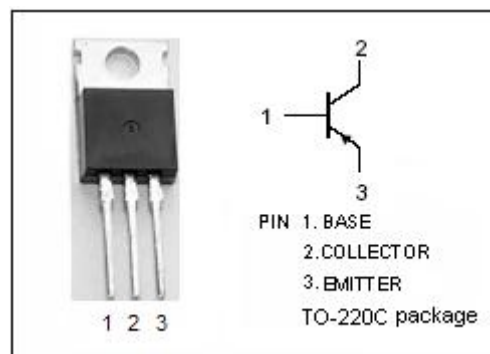
- Collector-Emitter Breakdown Voltage
: $V_{(BR)CEO} = -160V(\text{Min})$
- Good Linearity of h_{FE}
- Complement to Type 2SC2238

APPLICATIONS

- Power amplifier applications
- Driver stage amplifier applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-160	V
V_{CEO}	Collector-Emitter Voltage	-160	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-1.5	A
I_E	Emitter Current- Continuous	1.5	A
P_C	Total Power Dissipation @ $T_C=25^\circ\text{C}$	25	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



SPTECH Silicon PNP Power Transistor**2SA968****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -10mA ; I _B = 0	-160			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -1mA ; I _C = 0	-5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -0.5A ; I _B = -50mA			-1.5	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -0.5A ; V _{CE} = -5V			-1.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -160V ; I _E = 0			-1.0	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V ; I _C = 0			-1.0	μ A
h _{FE}	DC Current Gain	I _C = -0.1A ; V _{CE} = -5V	70		240	
C _{OB}	Output Capacitance	I _E = 0 ; V _{CB} = -10V ; f _{test} = 1MHz		30		pF
f _T	Current-Gain—Bandwidth Product	I _C = -0.1A ; V _{CE} = -10V		100		MHz

◆ **h_{FE} Classifications**

O	Y
70-140	120-240